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# BYT60P-400 BYT260PIV-400 / BYT261PIV-400

## FAST RECOVERY RECTIFIER DIODES

### MAIN PRODUCT CHARACTERISTICS

I <sub>F(AV)</sub>	2 x 60 A
V <sub>RMM</sub>	400 V
V <sub>F(max)</sub>	1.4 V
trr (max)	50 ns

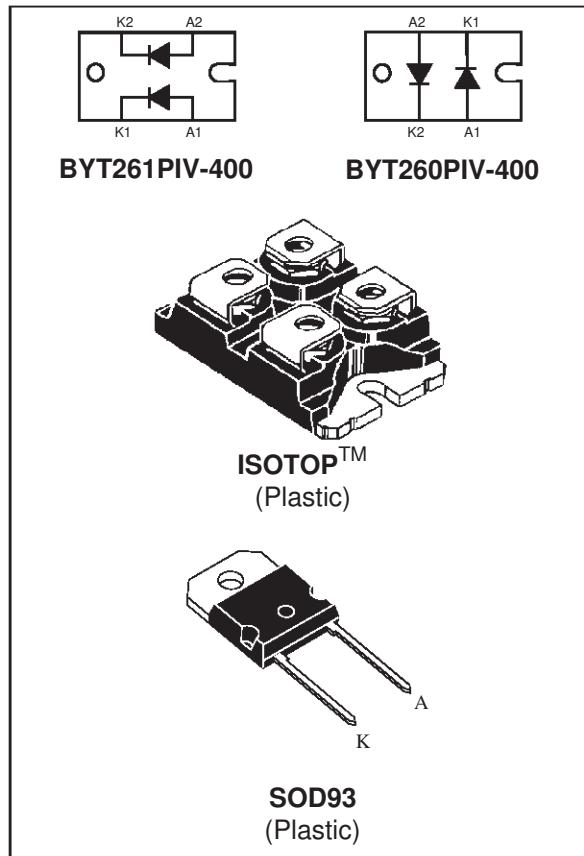
### FEATURES AND BENEFITS

- VERY LOW REVERSE RECOVERY TIME
- VERY LOW SWITCHING LOSSES
- LOW NOISE TURN-OFF SWITCHING
- INSULATED PACKAGE: ISOTOP  
Insulation voltage: 2500 V<sub>RMS</sub>  
Capacitance = 45 pF  
Inductance < 5 nH

### DESCRIPTION

These rectifier devices are suited for free-wheeling function in converters and motor control circuits.

Packaged in ISOTOP or SOD93, they are intended for use in Switch Mode Power Supplies.



### ABSOLUTE RATINGS (limiting values, per diode)

Symbol	Parameter		Value	Unit
V <sub>RMM</sub>	Repetitive peak reverse voltage		400	V
I <sub>FRM</sub>	Repetitive peak forward current	tp=5 µs F=1kHz	1000	A
I <sub>F(RMS)</sub>	RMS forward current	ISOTOP	140	A
		SOD93	100	
I <sub>F(AV)</sub>	Average forward current δ = 0.5	T <sub>c</sub> = 70°C	60	A
		T <sub>c</sub> = 80°C	SOD93	
I <sub>FSM</sub>	Surge non repetitive forward current tp = 10 ms Sinusoidal	ISOTOP	600	A
		SOD93	550	
T <sub>stg</sub>	Storage temperature range		- 40 to + 150	°C
T <sub>j</sub>	Maximum operating junction temperature		150	°C

TM: ISOTOP is a registered trademark of STMicroelectronics.

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### THERMAL RESISTANCES

Symbol	Parameter			Value	Unit
$R_{th(j-c)}$	Junction to case	ISOTOP	Per diode	0.8	$^{\circ}\text{C}/\text{W}$
		SOD93	Total	0.45	
$R_{th(c)}$			Total	0.7	
			Coupling	0.1	$^{\circ}\text{C}/\text{W}$

When the diodes 1 and 2 are used simultaneously :

$$\Delta T_j(\text{diode } 1) = P(\text{diode}) \times R_{th(j-c)} (\text{Per diode}) + P(\text{diode } 2) \times R_{th(c)}$$

### STATIC ELECTRICAL CHARACTERISTICS (per diode)

Symbol	Parameter	Test Conditions		Min.	Typ.	Max.	Unit
$V_F$ *	Forward voltage drop	$T_j = 25^{\circ}\text{C}$	$I_F = 60 \text{ A}$			1.5	V
		$T_j = 100^{\circ}\text{C}$				1.4	
$I_R$ **	Reverse leakage current	$T_j = 25^{\circ}\text{C}$	$V_R = V_{RRM}$			60	$\mu\text{A}$
		$T_j = 100^{\circ}\text{C}$				6	

Pulse test : \*  $t_p = 380 \mu\text{s}, \delta < 2\%$

\*\*  $t_p = 5 \text{ ms}, \delta < 2\%$

To evaluate the conduction losses use the following equation:

$$P = 1.1 \times I_F(AV) + 0.0045 I_F^2 (\text{RMS})$$

### RECOVERY CHARACTERISTICS (per diode)

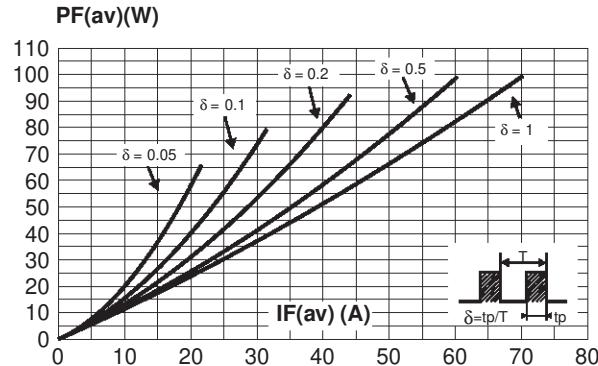
Symbol	Test Conditions			Min.	Typ.	Max.	Unit
$t_{rr}$	$T_j = 25^{\circ}\text{C}$	$I_F = 1\text{A}$	$V_R = 30\text{V}$	$dI_F/dt = -15\text{A}/\mu\text{s}$		100	ns
		$I_F = 0.5\text{A}$	$I_R = 1\text{A}$	$I_{rr} = 0.25\text{A}$		50	

### TURN-OFF SWITCHING CHARACTERISTICS

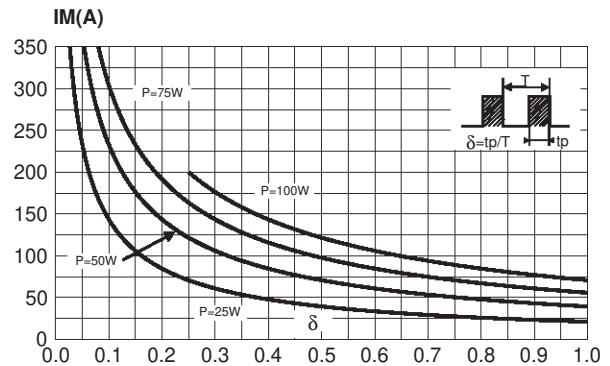
Symbol	Parameter	Test Conditions			Min.	Typ.	Max.	Unit
$t_{IRM}$	Maximum reverse recovery time	$dI_F/dt = -240 \text{ A}/\mu\text{s}$	$V_{CC} = 200 \text{ V}$	$I_F = 60 \text{ A}$			75	ns
		$dI_F/dt = -480 \text{ A}/\mu\text{s}$					50	
$I_{RM}$	Maximum reverse recovery current	$dI_F/dt = -240 \text{ A}/\mu\text{s}$	$L_p \text{ } 0.05 \mu\text{H}$	$T_j = 100^{\circ}\text{C}$			18	A
		$dI_F/dt = -480 \text{ A}/\mu\text{s}$					24	
$C = \frac{V_{RP}}{V_{CC}}$	Turn-off overvoltage coefficient	$T_j = 100^{\circ}\text{C}$	$V_{CC} = 120\text{V}$	$I_F = I_{F(AV)}$		3.3	4	/
		$dI_F/dt = -60\text{A}/\mu\text{s}$		$L_p = 0.8\mu\text{H}$				
		(see fig. 14)						

## BYT60P-400 / BYT260PIV-400 / BYT261PIV-400

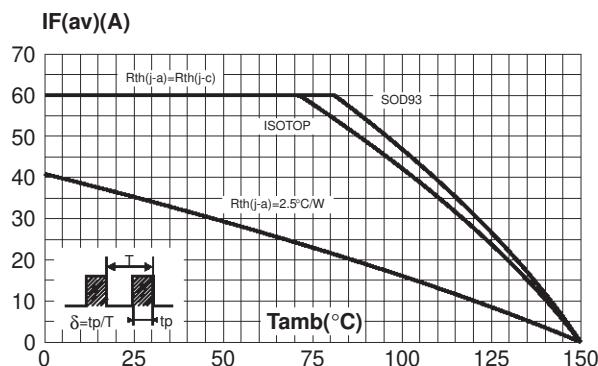
**Fig. 1:** Average forward power dissipation versus average forward current (per diode, for ISOTOP).



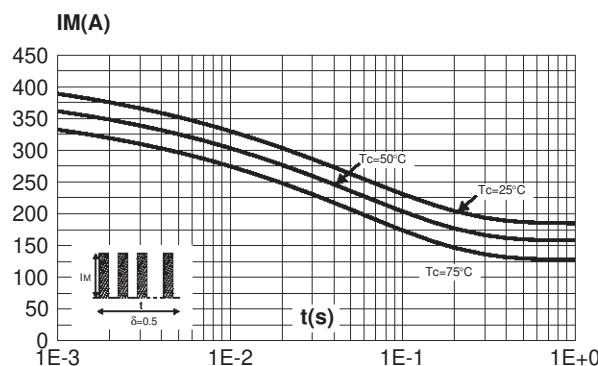
**Fig. 2:** Peak current versus form factor (per diode, for ISOTOP).



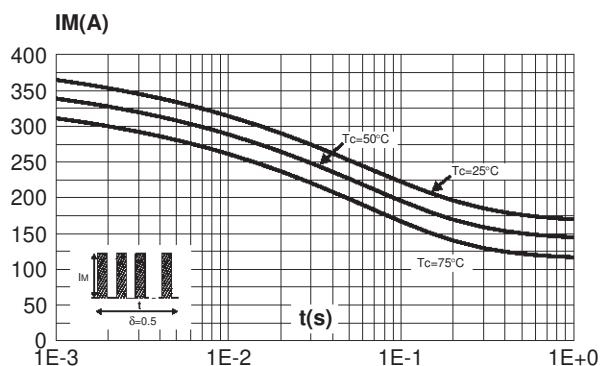
**Fig. 3:** Average forward current versus ambient temperature ( $\delta=0.5$ , per diode for ISOTOP).



**Fig. 4-1:** Non repetitive surge peak forward current versus overload duration (SOD93).

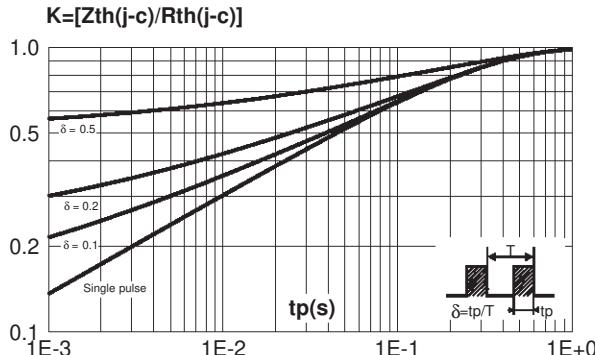


**Fig. 4-2:** Non repetitive surge peak forward current versus overload duration (per diode, for ISOTOP).

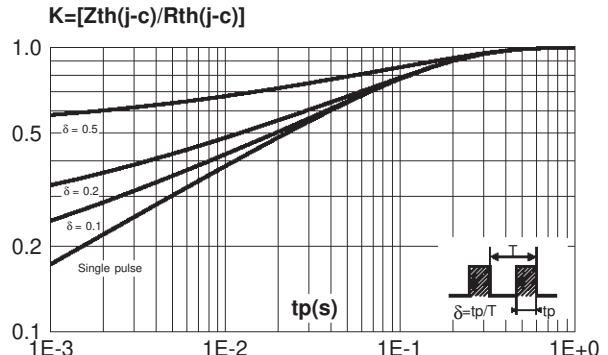


## BYT60P-400 / BYT260PIV-400 / BYT261PIV-400

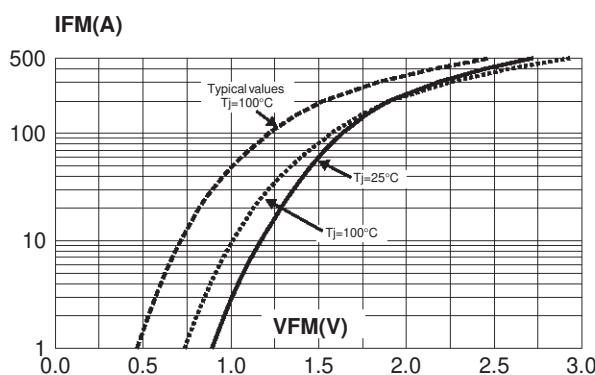
**Fig. 5-1:** Relative variation of thermal impedance junction to case versus pulse duration (per diode for ISOTOP).



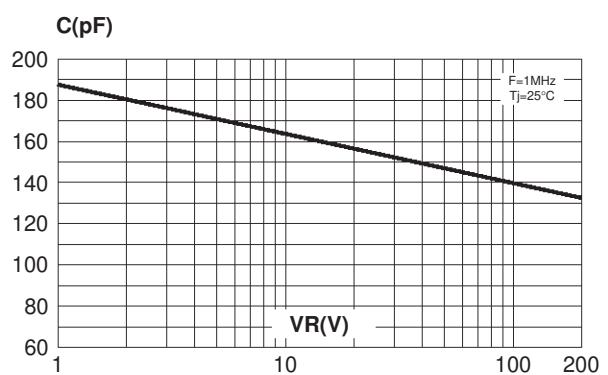
**Fig. 5-2:** Relative variation of thermal impedance junction to case versus pulse duration (SOD93).



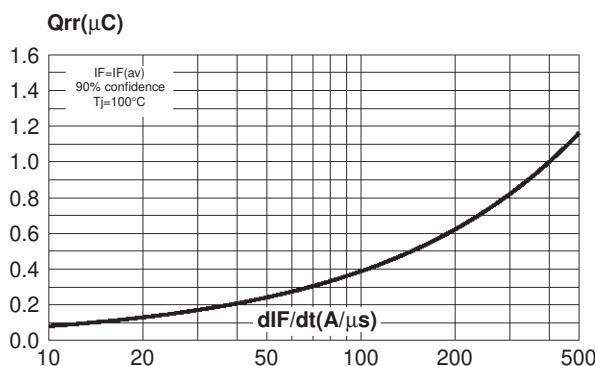
**Fig. 6:** Forward voltage drop versus forward current (maximum values, per diode for ISOTOP).



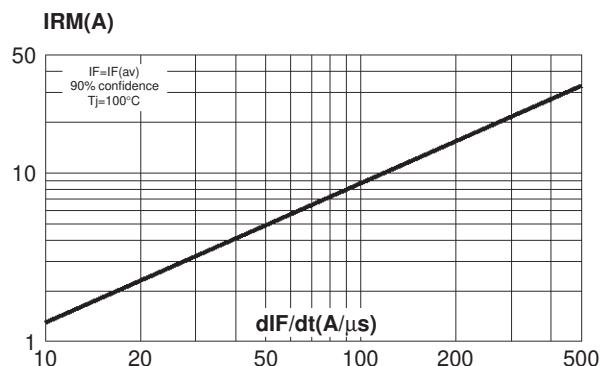
**Fig. 7:** Junction capacitance versus reverse voltage applied (typical values, per diode for ISOTOP).



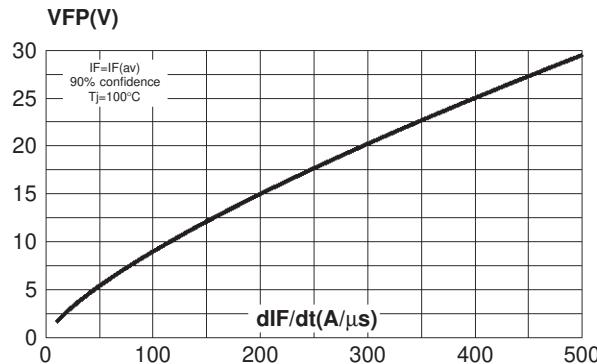
**Fig. 8:** Recovery charges versus  $dI_F/dt$  (per diode for ISOTOP).



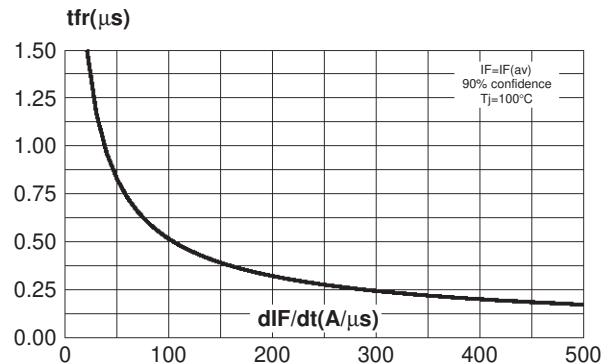
**Fig. 9:** Recovery current versus  $dI_F/dt$  (per diode for ISOTOP).



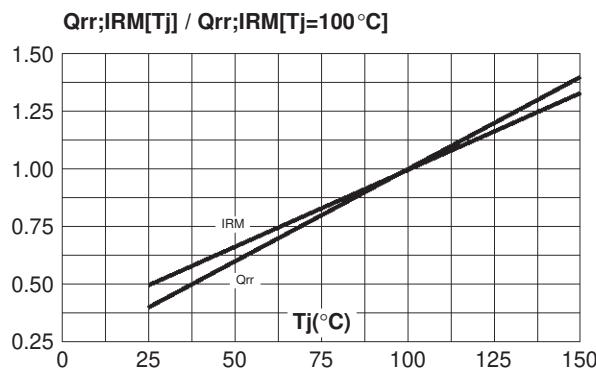
**Fig. 10:** Transient peak forward voltage versus  $dI_F/dt$  (per diode for ISOTOP).



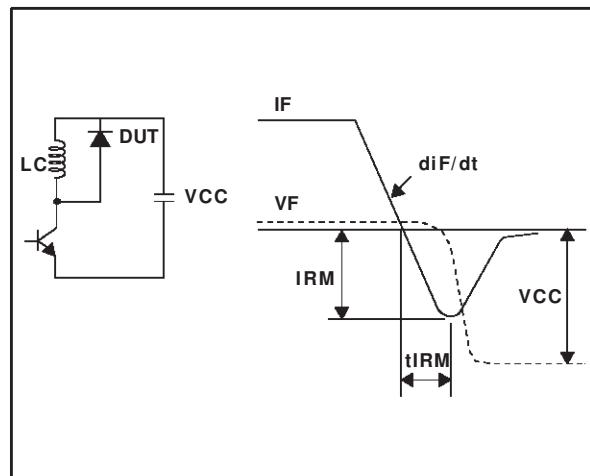
**Fig. 11:** Forward recovery time versus  $dI_F/dt$  (per diode for ISOTOP).



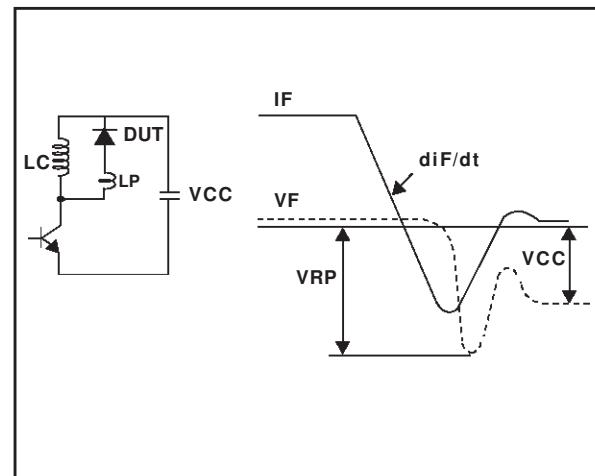
**Fig. 12:** Dynamic parameters versus junction temperature.



**Fig. 13:** Turn-off switching characteristics (without serie inductance).



**Fig. 14:** Turn-off switching characteristics (with serie inductance).

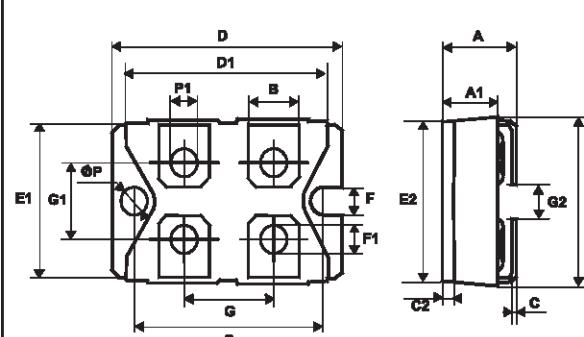


## **BYT60P-400 / BYT260PIV-400 / BYT261PIV-400**

### **PACKAGE MECHANICAL DATA**

ISOTOP

REF.	DIMENSIONS			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	11.80	12.20	0.465	0.480
A1	8.90	9.10	0.350	0.358
B	7.8	8.20	0.307	0.323
C	0.75	0.85	0.030	0.033
C2	1.95	2.05	0.077	0.081
D	37.80	38.20	1.488	1.504
D1	31.50	31.70	1.240	1.248
E	25.15	25.50	0.990	1.004
E1	23.85	24.15	0.939	0.951
E2	24.80 typ.		0.976 typ.	
G	14.90	15.10	0.587	0.594
G1	12.60	12.80	0.496	0.504
G2	3.50	4.30	0.138	0.169
F	4.10	4.30	0.161	0.169
F1	4.60	5.00	0.181	0.197
P	4.00	4.30	0.157	0.69



## PACKAGE MECHANICAL DATA

SOD93 Plastic

REF.	DIMENSIONS					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.70		4.90	0.185		0.193
C	1.17		1.37	0.046		0.054
D		2.50			0.098	
D1		1.27			0.050	
E	0.50		0.78	0.020		0.031
F	1.10		1.30	0.043		0.051
F3		1.75			0.069	
G	10.80		11.10	0.425		0.437
H	14.70		15.20	0.578		0.598
L			12.20			0.480
L2			16.20			0.638
L3		18.0			0.709	
L5	3.95		4.15	0.156		0.163
L6		31.00			1.220	
O	4.00		4.10	0.157		0.161

Ordering type	Marking	Package	Weight	Base qty	Delivery mode
BYT60P-400	BYT60P-400	SOD93	3.79 g.	30	Tube
BYT260PIV-400	BYT260PIV-400	ISOTOP	28 g. (without screws)	10	Tube
BYT261PIV-400	BYT261PIV-400	ISOTOP	28 g. (without screws)	10	Tube

- Cooling method: by conduction (C)
- Recommended torque value (ISOTOP): 1.3 N.m (MAX 1.5 N.m) for the 6 x M4 screws. (2 x M4 screws recommended for mounting the package on the heatsink and the 4 screws given with the screw version). The screws supplied with the package are adapted for mounting on a board (or other types of terminals) with a thickness of 0.6 mm min and 2.2 mm max.
- Recommended torque value (SOD93): 0.8 N.m.
- Maximum torque value (SOD93): 1.0 N.m.
- Epoxy meets UL94,V0

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